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Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

March 2015

MTD3055V*

N-Channel Enhancement Mode Field Effect Transistor

General Description

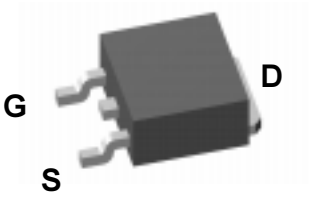
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable $R_{DS(ON)}$ specifications.

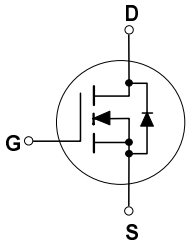
The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

Features

- 12 A, 60 V. $R_{DS(ON)}$ = 0.15 Ω @ V_{GS} = 10 V
- Low gate charge.
- Fast switching speed.
- High performance technology for low $R_{DS(ON)}$.



TO-252



Absolute Maximum Ratings

T_C=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DSS}	Drain-Source Voltage		60	V
V_{GSS}	Gate-Source Voltage		±20	V
I_D	Maximum Drain Current -Continuous	(Note 1)	12	A
	T_C = 100°C	(Note 1)	7.3	
	Maximum Drain Current -Pulsed		37	
P_D	Maximum Power Dissipation @ T_C = 25°C	(Note 1)	48	W
	T_A = 25°C	(Note 1a)	3.9	
	T_A = 25°C	(Note 1b)	1.5	
T_J, T_{STG}	Operating and Storage Junction Temperature Range		-55 to +175	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to- Case	(Note 1)	3.13	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to- Ambient	(Note 1a)	38	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
MTD3055V	MTD3055V	13”	16mm	2500

* Die and manufacturing source subject to change without prior notification.

Electrical Characteristics

T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
DRAIN-SOURCE AVALANCHE RATINGS (Note 2)						
w_{DSS}	Single Pulse Drain-Source Avalanche Energy	V_{DD} = 25 V, I_D = 12 A			72	mJ
I_{AR}	Maximum Drain-Source Avalanche Current				12	A
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA	60			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C		42		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 60 V, V_{GS} = 0 V			10	μA
		V_{DS} = 60 V, V_{GS} = 0 V, T_J = 150°C			100	
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 20 V, V_{DS} = 0 V			100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -20 V, V_{DS} = 0 V			-100	nA
On Characteristics (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 μA	2	2.8	4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C		-2.3		mV/°C
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 6 A,			0.15	Ω
$V_{DS(on)}$	Drain-Source On-Voltage On-Resistance	V_{GS} = 10 V, I_D = 12 A V_{GS} = 10 V, I_D = 6 A, T_J = 150°C			2.2 1.9	V
g_{FS}	Forward Transconductance	V_{DS} = 7 V, I_D = 6 A	4.0			S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz			500	pF
C_{oss}	Output Capacitance				180	pF
C_{rss}	Reverse Transfer Capacitance				50	pF
Switching Characteristics (Note 2)						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 30 V, I_D = 12 A, V_{GS} = 10 V, R_{GEN} = 9.1 Ω			10	ns
t_r	Turn-On Rise Time				60	ns
$t_{d(off)}$	Turn-Off Delay Time				30	ns
t_f	Turn-Off Fall Time				50	ns
Q_g	Total Gate Charge	V_{DS} = 48 V, I_D = 12 A, V_{GS} = 10 V		12.7	17	nC
Q_{gs}	Gate-Source Charge			3.2		nC
Q_{gd}	Gate-Drain Charge			7		nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current (Note 2)				12	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current (Note 2)				37	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 12 A (Note 2)			1.6	V
t_{rr}	Drain-Source Reverse Recovery Time	I_F = 12 A, di/dt = 100A/μs		46		nS

Notes:

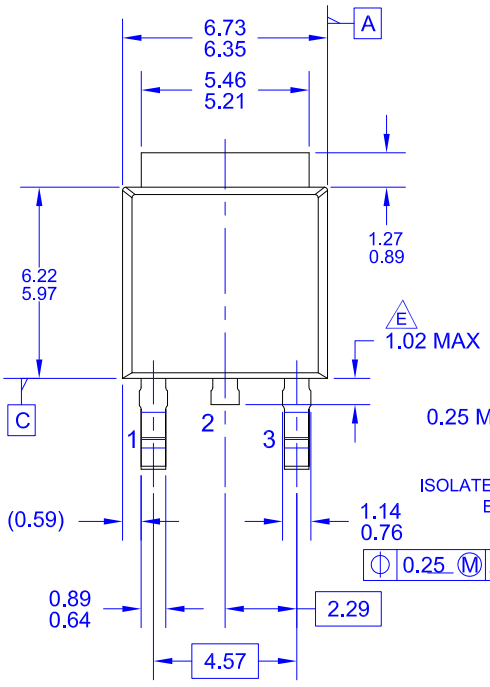
1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the drain tab. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.

a) $R_{\theta JA}$ = 38°C/W when mounted on a 1 in² pad of 2oz copper.

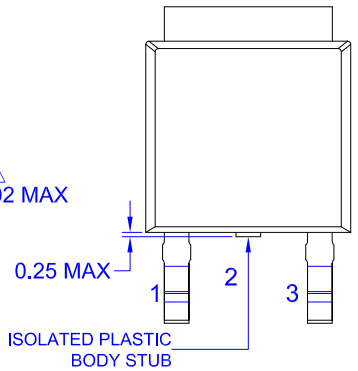
b) $R_{\theta JA}$ = 96°C/W when mounted on a minimuim pad.

Scale 1 : 1 on letter size paper

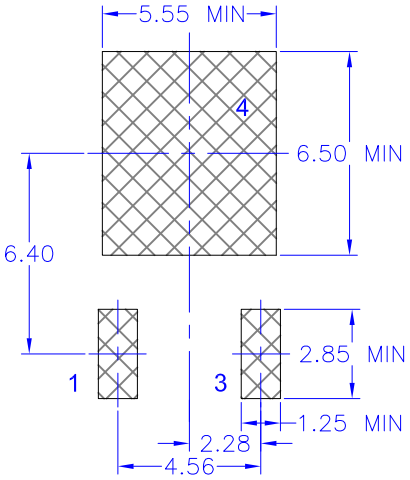
2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%



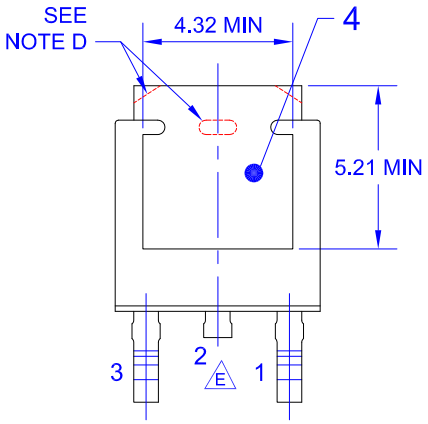
NON-DIODE PRODUCTS VERSION



DIODE PRODUCTS VERSION



LAND PATTERN RECOMMENDATION



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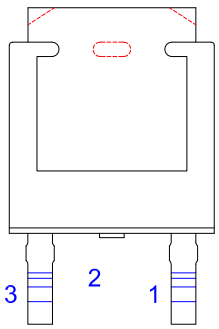

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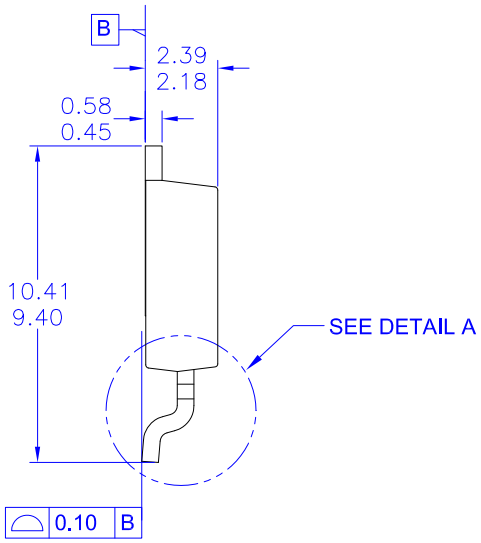
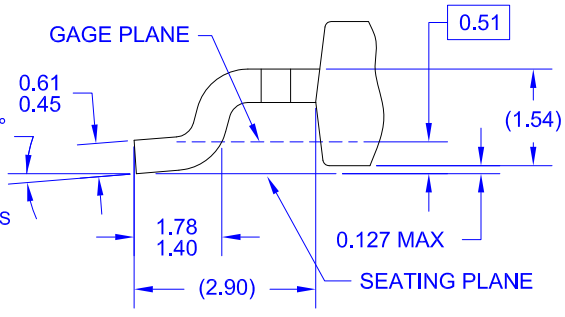


NOTES: UNLESS OTHERWISE SPECIFIED

A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION.
E) TRIMMED METAL CENTER LEAD IS PRESENT ON FOR NON-DIODE PRODUCTS
F) DIMENSIONS ARE EXCLUSIVE OF BURS, MOLD FLASH AND TIE BAR EXTRUSIONS.
G) LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD TO228P991X239-3N.
H) DRAWING NUMBER AND REVISION: MKT-TO252A03REV11



DETAIL A
(ROTATED -90°)
SCALE: 12X

FAIRCHILD

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